

FAST - (Untitled1:1)

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USPAT:US.PGRUB:GPO:PRO.DERVENT

Default operator: GR

(transistor or amplifier) and (control or controls) adj3 (channel adj length or channel adj width)

Document ID	Issue Date	Pages	Title	Current DR	Current XRef	Retrieval Class	Inventor	SS	CS	EP	JP	US
US 20040174762 A1	20040909	7	Deep power down switch for memory device	365/226			Suh, Jungwon	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
US 20040174349 A1	20040909	40	Driving circuits for displays	345/204			Ubsch, Frank Robert et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
US 20040170050 A1	20040902	27	Semiconductor integrated circuit device with improved storage MOSFET arrangement	365/149			Itoh, Kiyoo et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
US 20040166634 A1	20040826	11	Array architecture and process flow of nonvolatile memory devices for mass storage applications	438/262			Lee, Peter W. et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
US 20040165459 A1	20040826	12	Array architecture and process flow of nonvolatile memory devices for mass storage applications	365/200			Lee, Peter W. et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
US 20040152274 A1	20040805	7	Methods for manufacturing semiconductor devices	438/300	438/197; 438/299; 438/301; 438/268;		Park, Cheolsoo	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
US 20040142523 A1	20040722	15	Method of forming vertical mosfet with ultra-low on-resistance and low gate charge	438/197	438/270; 438/269;		Boncuys, Izak et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
US 20040140830 A1	20040722	18	Class AB digital to analog converter/line driver	327/65			Mulder, Jan et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
US 20040132256 A1	20040708	12	MOS transistor having a recessed gate electrode and fabrication method thereof	438/296	438/197; 438/270; 438/261;		Kim, Jae-Hun et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
US 20040132250 A1	20040708	75	Preventing dielectric thickening over a gate area of a transistor	438/264	257/E21.682; 257/E27.103; 257/E29.120;		Hazani, Emanuel	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
US 20040119100 A1	20040624	12	DENSE DUAL-PLANE DEVICES	257/204	257/206; 257/351; 438/178;		Nowak, Edward J. et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>

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